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IN4500

SWITCHING DIODE:

FEATURES

- SILICON HIGH FORWARD CONDUCTANCE SWITCHING DIODE
- VOIDLESS* HERMETICALLY SEALED GLASS PACKAGE
- METALLURGICALLY BONDED (-I TYPE)
TX, TXV TYPES AVAILABLE PER MIL-S-19500/403
- EXCLUDES DO-35 DUMET CONSTRUCTION OPTION.

MAXIMUM RATINGS

Operating Temperature: -65°C to $+175^{\circ}\text{C}$
Storage Temperature: -65°C to $+200^{\circ}\text{C}$
Surge Current: 4 Amps ($t_p = 1\mu\text{s}$)
Leakage Current: 100nA @ 75V, 25°C .

ELECTRICAL CHARACTERISTICS

at 25°C unless otherwise specified.

$V_{(BR)}$	V_{RWM} (working)	I_O (note 1)	I_f (surge) (1 sec)	I_f (surge) (1 μsec)	T_{OP}	T_{STG}
Vdc	V(pk)	mAdc	A	A	$^{\circ}\text{C}$	$^{\circ}\text{C}$
80	75	300	0.5	4.0	-65 to $+175$	-65 to $+200$

CAPACITANCE $V_R = 0$ Volts $V_{sig} = 50$ mVpp $100\text{KHz} \leq f \leq 1$ MHz	V_{I1} @ $I_f = 250\mu\text{Adc}$	V_{I2} @ $I_f = 1.0\text{mA}$	V_{I3} @ $I_f = 10\text{mA}$	V_{I4} @ $I_f = 20\text{mA}$	V_{I5} @ $I_f = 300\text{mA}$ (pulse)	I_{rr} @ $I_f = I_{RT}$ 10mAdc $R_L = 100$ ohms
pF	Vdc	Vdc	Vdc	Vdc	Vdc	ns
4 max.	.47 - .56	.52 - .60	.64 - .72	.67 - .77	1.1 max.	6.0 max.

OTE 1: DERATE 2.0 mAdc/ $^{\circ}\text{C}$ For T_A Above 25°C .

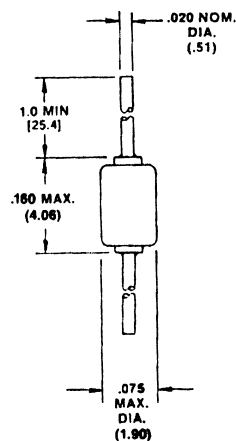
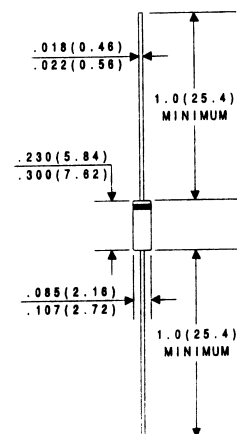


FIGURE 1
PACKAGE DO-35

DO-35 Package



DO-7 Package